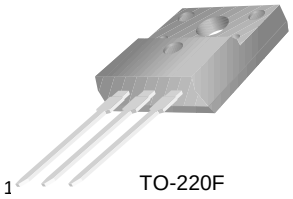
FJPF5021

High Voltage and High Reliability

- High Speed Switching : t_F = 0.1μs(Typ.)
- Wide SOA



TO-220F

1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	5	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current	2	A
P_C	Collector Dissipation (T_C=25°C)	40	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 1mA, I_E = 0	800			V
BV_{CEO}	Collector-Emitter Sustaining Voltage	I_C = 5mA, I_B = 0	500			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1mA, I_C = 0	7			V
V_{CEX} (sus)	Collector-Emitter Sustaining Voltage	I_C = 2.5A, I_{B1} = -I_{B2} = 1A L = 1mH, Clamped	500			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 500V, I_E = 0			10	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V, I_C = 0			10	μA
h_{FE1} h_{FE2}	DC Current Gain	V_{CE} = 5V, I_C = 0.6A V_{CE} = 5V, I_C = 3A	15 8		50	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 3A, I_B = 0.6A			1	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 3A, I_B = 0.6A			1.5	V
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0, f = 1MHz		80		pF
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.6A		15		MHz
t_{ON}	Turn On Time	V_{CC} = 200V I_C = 5I_{B1} = -2.5I_{B2} = 4A R_L = 50Ω			0.5	μs
t_{STG}	Storage Time				3	μs
t_F	Fall Time			0.1	0.3	μs

h_{FE} Classification

Classification	R	O	Y
h_{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

Typical Characteristics

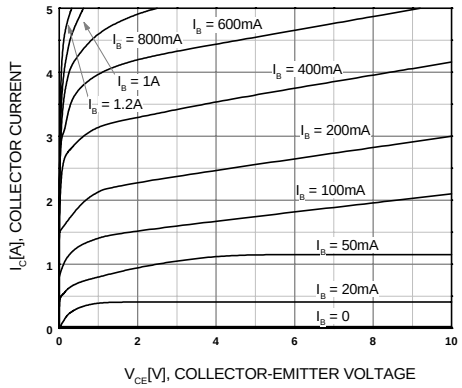


Figure 1. Static Characteristic

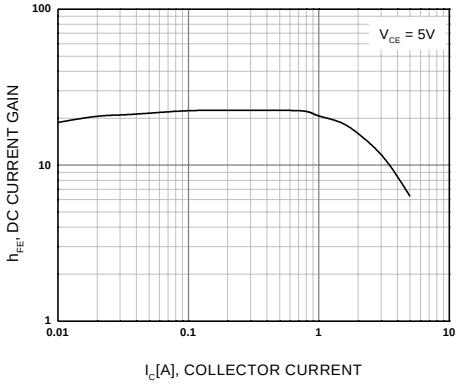


Figure 2. DC current Gain

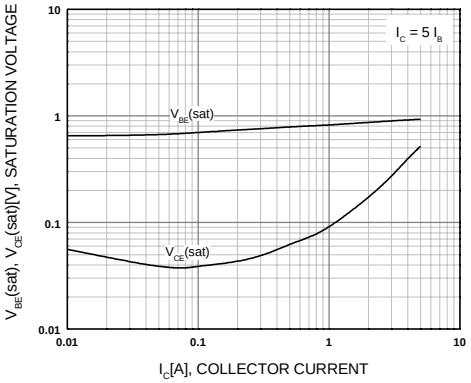


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

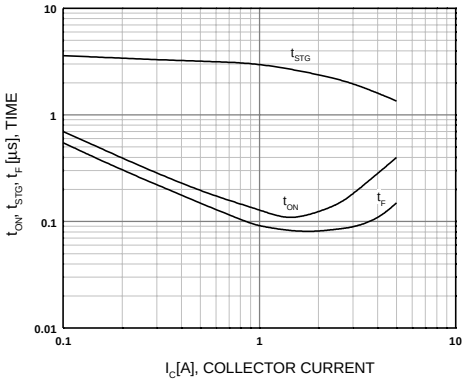


Figure 4. Switching Time

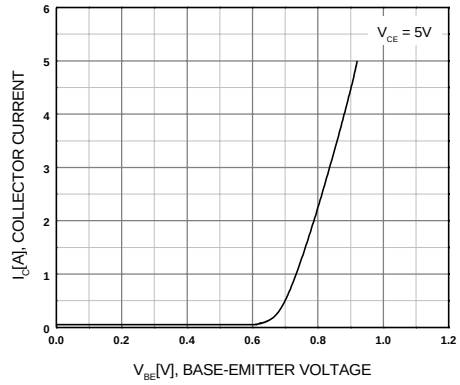


Figure 5. Base-Emitter On Voltage

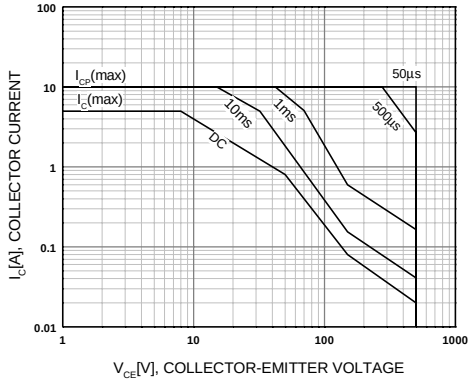


Figure 6. Forward Bias Safe Operating Area

Typical Characteristics (Continued)

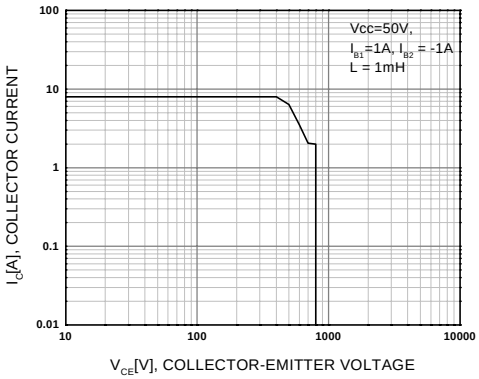


Figure 7. Reverse Bias Safe Operating Area

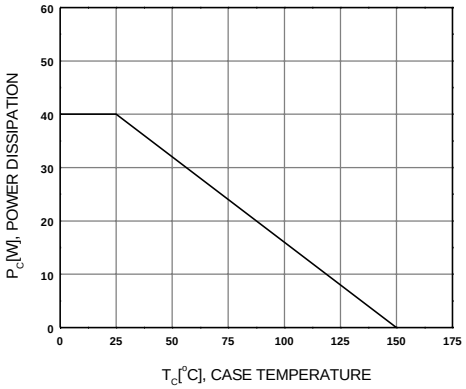
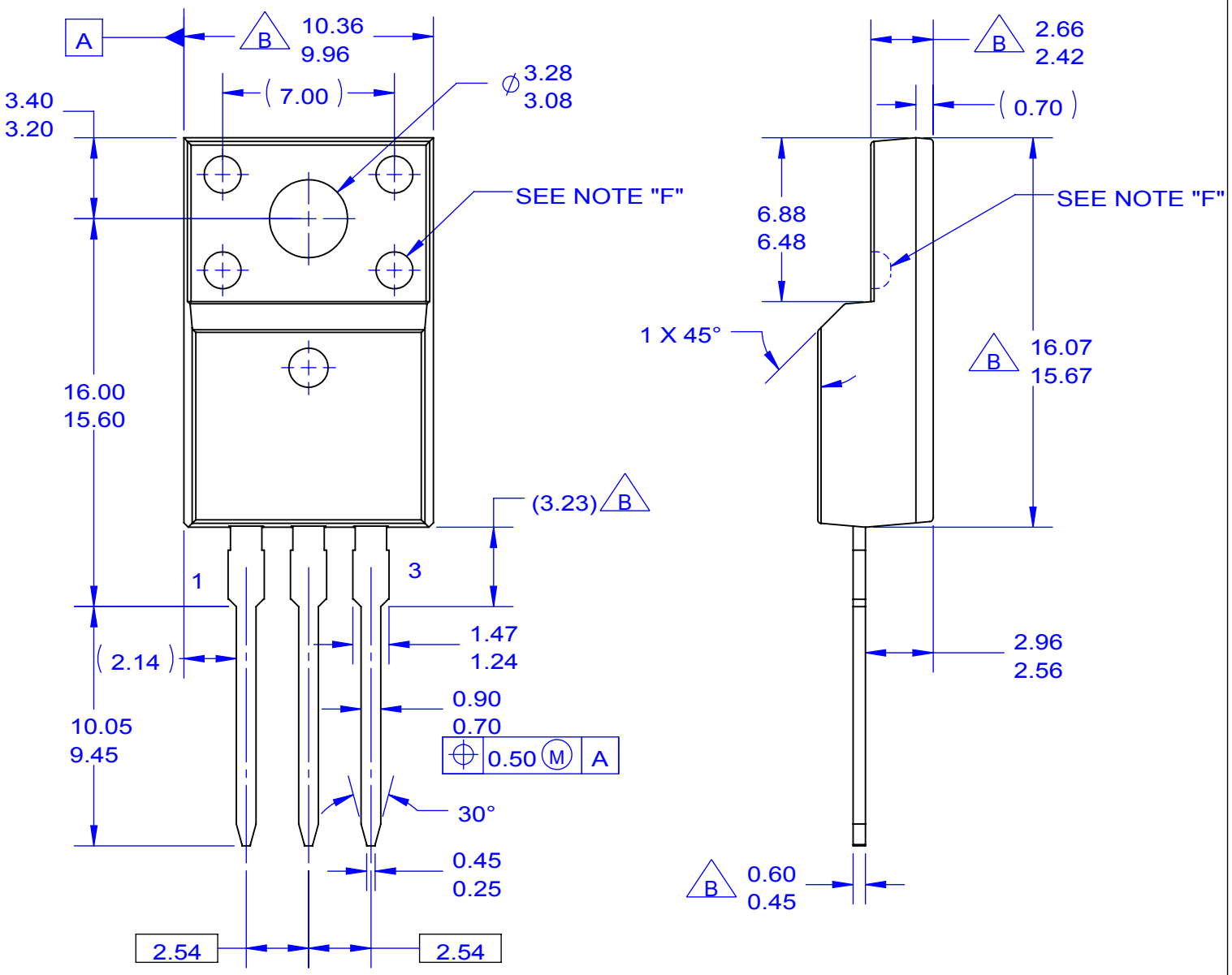
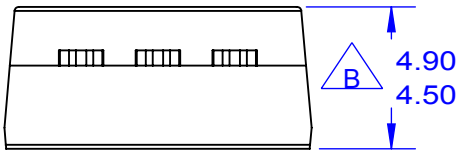


Figure 8. Power Derating





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NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
B DOES NOT COMPLY EIAJ STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
G. DRAWING FILE NAME: TO220M03REV5

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